



# isc Silicon NPN Power Transistor

#### **DESCRIPTION**

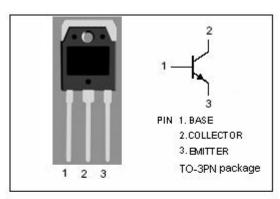
- · High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 800V(Min)
- · Fast Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

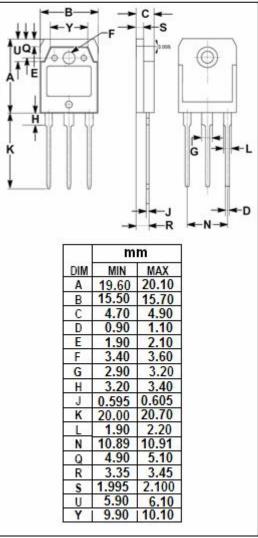
### **APPLICATIONS**

- · Switching regulator and high voltage switching applications
- High speed DC-DC converter applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	900	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	Α		
Ісм	Collector Current-Peak	20	Α	
I <sub>B</sub>	Base Current-Continuous	3	Α	
Pc	Pc Collector Power Dissipation @ T <sub>C</sub> =25°C		W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	${\mathbb C}$	





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2SC3153

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; R <sub>BE</sub> = ∞	800			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	900			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μ <b>А</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.4A; V <sub>CE</sub> = 5V	10		40	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	8			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.4A; V <sub>CE</sub> = 10V		15		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V		120		pF
Switching ti	imes		1		1	1
t <sub>r</sub>	Rise Time				1.0	μ <b>S</b>
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4A;I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A; R <sub>L</sub> = 100 Ω; V <sub>CC</sub> = 400V			3.0	μS
t <sub>f</sub>	Fall Time	, ==			0.7	μS

### ♦ h<sub>FE-1</sub> Classifications

K	L	M
10-20	15-30	20-40

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